

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,849,901 B2  
DATED : February 1, 2005  
INVENTOR(S) : Falster

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

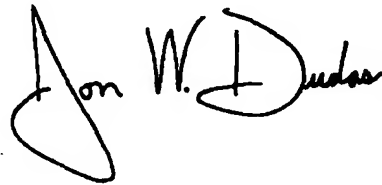
Title page,

Item [54], Title, should read:

-- **SILICON-ON-INSULATOR STRUCTURE HAVING A DEVICE LAYER  
WHICH IS VACANCY DOMINATED AND SUBSTANTIALLY FREE OF  
AGGLOMERATED VACANCY-TYPE DEFECTS** --.

Signed and Sealed this

Thirteenth Day of December, 2005

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is stylized, with the first name "Jon" and last name "Dudas" clearly legible, and "W." in the middle.

JON W. DUDAS  
*Director of the United States Patent and Trademark Office*